

A 32 X 32 DOPED SILICON BASED MATRIX READ BY HEMT/SIGE CRYO-ELECTRONICS

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Abstract

Since a decade, CEA have started a long term program to achieve the collective realization of a large (32 x 32 pixels) microcalorimeters camera for X-ray Astrophysics. This camera is based on silicon doped sensors with composite Tantalum absorber readout thanks to HEMT/SiGe based Cryo-electronics. The goal of this development is to achieve a spectral resolution of about 2 eV @ 6 keV in a thermal budget of ~1 µW @ 50 mK for over than 4000 pixels.

After some delays in production, we present the design of our first 32x32 sensors matrix. We also present the steps of the development plan of first measurements onto our matrix.

Goals

Scientific Goals:

Spatial X-ray observation

- \succ Large Field of View \Rightarrow a lot of relatively big pixels
- > Homogeneity of FoV \Rightarrow All pixels/readout should be similar

Technical choices:

- All-Silicon collective design
- Cryo-Electronics (@2.5-4 K) based on HEMTs and SiGe ASICs.
- > 34 : 1 "classic" Multiplexing
- First electronics stage @ 2.5-4 K and polarization resistance @ 300 mK ⇒ Ultra-Low consumption @ 50 mK

Pixel :

- ➢ 500 µm x 500 µm ~2 eV @ 6 keV
- High Z absorber: Superconducting hybrid Tantalum absorber
- Sensor M.I.S. Si:P:B

Thermal decoupling :

- Multilayers between 50 mK and 300 mK
- Superconducting Nb flexible between 300 mK and 2.5 4 K

System and camera

Camera:

> 4 Independent quadrants of 2 sides buttable 32 x 32 pixel matrices





Production of 15 4-inch-wafers

Validation wafer extracted before last step of production before DRIE



Thermal parameters



Last step: Back etching DRIE to make pixels free

And hybridization of sensors with composite Ta

Aknowledgements and references

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> References:

- > 1. J.L. Sauvageot et al., Toward large μ-calorimeters X-ray matrices based on metal-insulator sensors and HEMTs/SiGe cryo-electronics Proc. SPIE 9905, 99050S-1 (2016). https://doi.org/10.1117/12.2232397
- 2. Galahad Jego PhD thesis , Université d'Orsay (2019)
- 3. X. de la Broise et al. Proceedings of LTD17 Kurume, J. Low Temp. Phys. (2018) 193, 578-584 DOI: 10.1007/s10909-018-1930-3
- ➢ 4. J-L Sauvageot et al. Proceedings of SPIE
- 5. G. Jego et al., J. Low Temp. Phys., This Special Issue (2019)

